



General Description

The MAX17121 includes two high-voltage level-shifting scan drivers for TFT panel integrated gate logic. Each scan driver has two channels that switch complementarily. The scan-driver outputs swing from +40V to -30V and can swiftly drive capacitive loads. In order to save power, the scan driver's complementary outputs share the charge of their capacitive load before they change states.

The MAX17121 is available in a 24-pin, 4mm x 4mm, thin QFN package with a maximum thickness of 0.8mm for ultra-thin LCD panels.

Applications

Notebook Computer Displays LCD Monitor and Small TV Panels

Features

- ♦ +40V to -30V Output Swing Range
- ♦ Fast Slew Rate for High Capacitive Load
- **♦ Load Charge Sharing for Power Saving**
- ♦ 24-Pin, 4mm x 4mm, Thin QFN Package

Ordering Information

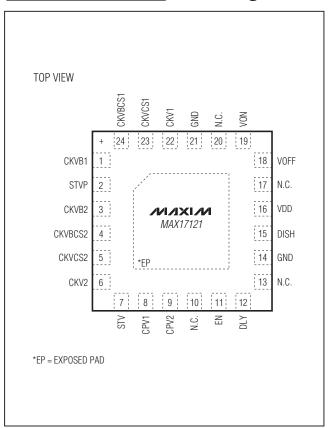
PART	TEMP RANGE	PIN-PACKAGE
MAX17121ETG+	-40°C to +85°C	24 TQFN-EP*

^{*}EP = Exposed pad.

Simplified Operating Circuit

$V_{VOFF} = -15V$ $V_{VON} = 25V$ GND NOV VOFF EQUIVALENT LOAD OF DISPLAY PANEL CKVB1 N.C. STVP N.C N.C CKVB2 MIXIM 200Ω N.C CKVBCS2 MAX17121 CKVCS2 200Ω CKV2 STV $V_{VDD} = 3.3V$ DISH GND GND VDD \equiv PLY STV T-CON CPV/1 CPV2

Pin Configuration



Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

VDD to GND	0.3V to +4V
CPV1, CPV2, STV, EN to GND	0.3V to +4V
DLY to GND	0.3V to (V _{VDD} + 0.3V)
DISH to GND	6V to (V _{VDD} + 0.3V)
VON to GND	0.3V to +45V
VOFF to GND	35V to + 0.3V
VON to VOFF	+65V
CKV1, CKV2, CKVB1, CKVB2,	
to VOFF	0.3V to (V _{VON} + 0.3V)

STVP to VOFF	$-0.3V$ to $(V_{VON} + 0.3V)$
CKVCS1, CKVCS2 to VOFF	$-0.3V$ to $(VVON + 0.3V)$
CKVBCS1, CKVBCS2 to VOFF	$-0.3V$ to $(V_{VON} + 0.3V)$
Continuous Power Dissipation (TA =	+70°C)
24-Pin, 4mm x 4mm Thin QFN	
(derate 27.8mW/°C above +70°C).	2222.2mW
Operating Temperature Range	40°C to +85°C
Junction Temperature	
Storage Temperature Range	
Lead Temperature (soldering, 10s)	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(VVDD = VEN = +3.3V, VVON = 25V, VVOFF = -15V, STV = CPV1 = CPV2 = GND, $T_A = 0^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
VDD Input Voltage Range		2.2	-	3.6	V	
VDD UV Lockout	Rising, hysteresis = 150mV		2	2.15	V	
VDD Oviges and Comment	V _{EN} = 3.3V		250	400		
VDD Quiescent Current	EN = GND		250	400	μΑ	
Thermal Shutdown	Rising edge, hysteresis = 15°C		+160		°C	
VON Input Voltage Range		15		40	V	
VON Current	VEN = 3.3V		300	600		
VON Supply Current	EN = GND		300	600	μΑ	
VOFF Input Voltage Range		-30		-3	V	
VOEE Comply Correct	V _{EN} = 3.3V		200	300		
VOFF Supply Current	EN = GND		200	300	- μΑ	
VON-to-VOFF Voltage Range			-	65	V	
VON UV Lockout	VON rising		12	13	V	
VON OV LOCKOUL	VON falling	10	11			
CKV_, CKVB_ Output Low	$I(CKV_{-}) = -20mA$		5	10	Ω	
CKV_, CKVB_ Output High	I(CKV_) = 20mA		9	18	Ω	
CPV_ Rising to CKV_ Rising	t _R , Figure 4, V _{STV} = 0V		100	150	ns	
CPV_ Rising to CKV_ Falling	tF, Figure 4, VSTV = 0V		100	150	ns	
CPV_ Rising to CKVB_ Rising	t _R , Figure 4, V _{STV} = 0V		100	150	ns	
CPV_ Rising to CKVB_ Falling	tF, Figure 4, VSTV = 0V		100	150	ns	
CPV_ Falling to CKVCS_ Rising	t _{CSR} , Figure 4, V _{STV} = 0V		100	150	ns	
CPV_ Falling to CKVCS_ Falling	tcsf, Figure 4, Vstv = 0V		100	150	ns	
CPV_ Falling to CKVCBS_ Rising	t _{CSR} , Figure 4, V _{STV} = 0V		100	150	ns	
CPV_ Falling to CKVBCS_ Falling	t _{CSF} , Figure 4, V _{STV} = 0V		100	150	ns	

ELECTRICAL CHARACTERISTICS (continued)

(VVDD = VEN = +3.3V, VVON = 25V, VVOFF = -15V, STV = CPV1 = CPV2 = GND, $T_A = 0^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
CKV_, CKVB_ Slew Rate Rising	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100 Ω , 15% to 85% (Note 1)	100	1400		V/µs
	STV = GND, C _{LOAD} = 4.7nF, 20% to 80%	100	160		
CKV_, CKVB_ Slew Rate Falling	STV = GND, CLOAD = 15nF, RLOAD = 100Ω , 85% to 15% (Note 1)	100	2000		V/µs
	STV = GND, C _{LOAD} = 4.7nF, 80% to 20%	100	160		
CKV_, CKVB_ Slew Rate Rising	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100 Ω , 15% to 85% (Note 1)	100	1400		V/µs
	STV = VDD, C _{LOAD} = 4.7nF, 20% to 80%	100	160		
CKV_, CKVB_ Slew Rate Falling	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100 Ω , 85% to 15% (Note 1)	100	2400		V/µs
	STV = VDD, C _{LOAD} = 4.7nF, 80% to 20%	100	160		
Three-State Output Current	CKV = midsupply (Note 2)	-1		+1	μΑ
CKVCSto-CKVBCS_ Resistance	I(CKVCS_ to CKVBCS_) = 10mA		40	100	Ω
STVP Output Low	I(STVP) = -20mA		5	10	Ω
STVP Output High	I(STVP) = 20mA		18	35	Ω
STV Rising to STVP Rising			100	200	ns
STV Falling to STVP Falling			100	200	ns
STVP Slew Rate Rising	C1 = 4.7 nF, R1 = 200Ω (Note 1) C1 = 4.7 nF	50 50	1000		V/µs
	C1 = 4.7nF, R1 = 200Ω (Note 1)	50	2000		
STVP Slew Rate Falling	C1 = 4.7nF	50	100		V/µs
CPV_ Input Frequency				85	kHz
Input Low Voltage	CPV_, STV, EN, 2.2V ≤ V _{VDD} ≤ 3.6V			0.8	V
Input High Voltage	CPV_, STV, EN, 2.2V ≤ V _{VDD} ≤ 3.6V	2.1			V
Input Hysteresis	CPV_, STV, EN		250		mV
Input-Bias Current	VSTV_ = 0V or VyDD; VCPV_ = 0V or VyDD (Note 2)	-1		+1	μΑ
DISH Low Voltage			-0.66	-1.5	V
DISH High Voltage		-0.5	-0.65		V
DISH Hysteresis			10		mV
DISH Input Impedance	V _{DISH} = -2V		300	600	kΩ
DIOLLO 3. L D. S. L	V _{DISH} = -2V		200	500	Ω
DISH Switch Resistance	VDISH = 0V		1		МΩ
DLY Output Current	DLY = GND	3	4	5	μΑ
DLY Sink Current	EN = GND, V _{DLY} = 0.4V	5	8		mA
DLY Enable Threshold	Rising, hysteresis = 100mV	1.60	1.65	1.70	V
Startup Delay	$C(DLY) = 0.1\mu F$		40		ms

ELECTRICAL CHARACTERISTICS

 $(VVDD = VEN = +3.3V, VVON = 25V, VVOFF = -15V, STV = CPV1 = CPV2 = GND, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.})$ (Note 2)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS		
VDD Input Voltage Range		2.2		3.6	V		
VDD UV Lockout	Rising, hysteresis = 150mV			2.15	V		
VDD Ovices and Overent	V _{EN} = 3.3V			400			
VDD Quiescent Current	EN = GND			400	μΑ		
Thermal Shutdown	Rising edge, hysteresis = 15°C				°C		
VON Input Voltage Range		15		40	V		
VON Supply Current	V _{EN} = 3.3V			600			
VON Supply Current	EN = GND			600	μΑ		
VOFF Input Voltage Range		-30		-3	V		
VOEE Supply Current	VEN = 3.3V			300			
VOFF Supply Current	EN = GND			300	μΑ		
VON-to-VOFF Voltage Range				65	V		
VON UV Lockout	VON rising			13	V		
VON OV LOCKOUL	VON falling	10			7 V		
CKV_, CKVB_ Output Low	I(CKV_) = -20mA			10	Ω		
CKV_, CKVB_ Output High	I(CKV_) = 20mA			18	Ω		
CPV_ Rising to CKV_ Rising	tR, Figure 4, VSTV = 0V			150	ns		
CPV_ Rising to CKV_ Falling	t _F , Figure 4, V _{STV} = 0V			150	ns		
CPV_ Rising to CKVB_ Rising	t _R , Figure 4, V _{STV} = 0V			150	ns		
CPV_ Rising to CKVB_ Falling	t _F , Figure 4, V _{STV} = 0V			150	ns		
CPV_ Falling to CKVCS_ Rising	tcsr, Figure 4, Vstv = 0V			150	ns		
CPV_ Falling to CKVCS_ Falling	tcsf, Figure 4, Vstv = 0V			150	ns		
CPV_Falling to CKVCBS_Rising	tcsr, Figure 4, Vstv = 0V			150	ns		
CPV_ Falling to CKVBCS_ Falling	tcsf, Figure 4, Vstv = 0V			150	ns		
CKV_, CKVB_ Slew Rate Rising	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100 Ω , 15% to 85% (Note 2)	100			V/µs		
	STV = GND, C _{LOAD} = 4.7nF, 20% to 80%	100					
CKV_, CKVB_ Slew Rate Falling	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100 Ω , 85% to 15% (Note 2)				V/µs		
-	STV = GND, CLOAD = 4.7nF, 80% to 20%	100					
CKV_, CKVB_ Slew Rate Rising	STV = VDD, CLOAD = 15nF, RLOAD = 100Ω , 15% to 85% (Note 2)	100			V/µs		
	STV = VDD, C _{LOAD} = 4.7nF, 20% to 80%	100					
CKV_, CKVB_ Slew Rate Falling	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100 Ω , 85% to 15% (Note 2)	100			V/µs		
	STV = VDD, C _{LOAD} = 4.7nF, 80% to 20%	100					

ELECTRICAL CHARACTERISTICS (continued)

 $(VVDD = VEN = +3.3V, VVON = 25V, VVOFF = -15V, STV = CPV1 = CPV2 = GND, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.})$ (Note 2)

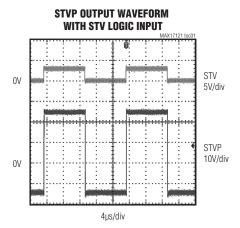
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
CKVCSto-CMVBCS Resistance	I(CKVCSto-CKVBCS) = 10mA			100	Ω
STVP Output Low	I(STVP) = -20mA			10	Ω
STVP Output High	I(STVP) = 20mA			35	Ω
STV Rising to STVP Rising				200	ns
STV Falling to STVP Falling				200	ns
STVP Slew Rate Rising	$C_L = 4.7 nF$	50			V/µs
STVP Slew Rate Falling	C _L = 4.7nF	50			V/µs
CPV_ Input Frequency				85	kHz
Input Low Voltage	CPV_, STV, EN, 2.2V ≤ V _{VDD} ≤ 3.6V			0.8	V
Input High Voltage	CPV_, STV, EN, 2.2V ≤ V _{VDD} ≤ 3.6V	2.1		-	V
Input Hysteresis	CPV_, STV, EN				mV
DISH Low Voltage				-1.5	V
DISH High Voltage		-0.5			V
DISH Hysteresis					mV
DISH Input Impedance	V _{DISH} = -2V			600	kΩ
DISH Switch Resistance	VDISH = -2V			500	Ω
DLY Output Current	DLY = GND	3		5	μΑ
DLY Sink Current	EN = GND, V _{DLY} = 0.4V	5			mA
DLY Enable Threshold	Rising	1.60		1.70	V

Note 1: Guaranteed by design. Not production tested.

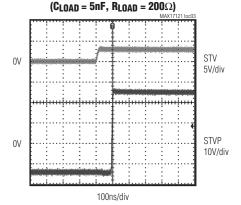
Note 2: Limits are 100% production tested at T_A = +25°C. Maximum and minimum limits over temperature are guaranteed by design and characterization.

Typical Operating Characteristics

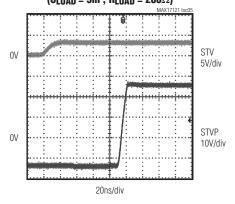
(Circuit of Figure 1, VVDD = VEN = 3.3V, VVON = 25V, VVOFF = -15V, T_A = +25°C, unless otherwise noted.)



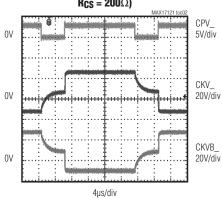
STV-TO-STVP RISING EDGE PROPAGATION DELAY



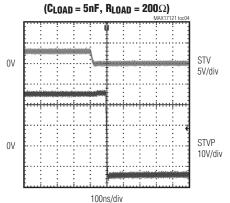
STVP SLEW RATE ON RISING EDGE (CLOAD = 5nF, RLOAD = 200 Ω)



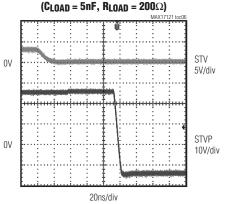
CKV_ AND CKVB_ OUTPUT WAVEFORMS WITH CPV LOGIC INPUT (STV = 0V, CLOAD = 5nF, RLOAD = 50Ω , RCS = 200Ω)



STV-TO-STVP FALLING EDGE PROPAGATION DELAY



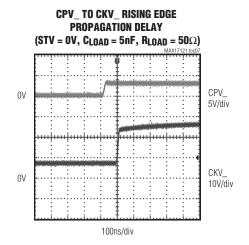
STVP SLEW RATE ON FALLING EDGE

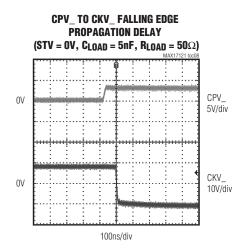


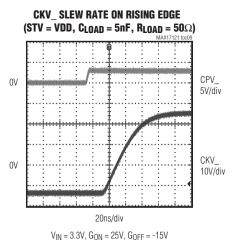
V_{IN} = 3.3V, G_{ON} = 25V, G_{OFF} = 15V

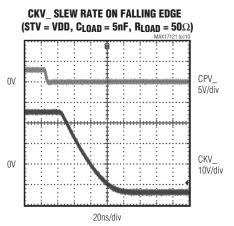
Typical Operating Characteristics (continued)

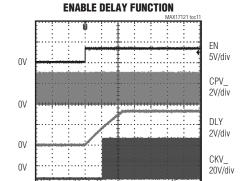
(Circuit of Figure 1, VVDD = VEN = 3.3V, VVON = 25V, VVOFF = -15V, T_A = +25°C, unless otherwise noted.)











40ms/div

Pin Description

PIN	NAME	FUNCTION			
1	CKVB1	High-Voltage Scan-Drive Output. CKVB1 is the inverse of CKV1 during active states and is high impedance whenever CKV1 is high impedance.			
2	STVP	High-Voltage Scan-Drive Output. STVP is connected to VOFF when STV is low and is connected to VON when STV is high and CPV1 is low. When both STV and CPV1 are high, STVP is high impedance.			
3	CKVB2	High-Voltage Scan-Drive Output. CKVB2 is the inverse of CKV2 during active states and is high impedance whenever CKV2 is high impedance.			
4	CKVBCS2	CKVB2 Charge-Sharing Connection. CKVBCS2 connects to CKVCS2 whenever CPV2 and STV are both low (to make CKV2 and CKVB2 high impedance) to allow CKV2 to connect to CKVB2, sharing charge between the capacitive loads on these two outputs.			
5	CKVCS2	CKV2 Charge-Sharing Connection. CKVCS2 connects to CKVBCS2 whenever CPV2 and STV are both low (to make CKV2 and CKVB2 high impedance) to allow CKVB2 to connect to CKV2, sharing charge between the capacitive loads on these two outputs.			
6	CKV2	High-Voltage Scan-Drive Output. When enabled, CKV2 toggles between its high state (connected to VON) and its low state (connected to VOFF) on each falling edge of the CPV2 input. Further, CKV2 is high impedance whenever CPV2 and STV are both low.			
7 STV		Vertical Sync Input. The rising edge of STV begins a frame of data. The STV input is used to generate the high-voltage STVP output.			
8	CPV1	Vertical Clock-Pulse Input. CPV1 controls the timing of the CKV1 and CKVB1 outputs, which change state (by first sharing charge) on its falling edge.			
9	CPV2	Vertical Clock-Pulse Input. CPV2 controls the timing of the CKV2 and CKVB2 outputs, which change state (by first sharing charge) on its falling edge.			
10, 13, 17, 20	N.C.	Not Connected			
11	EN	Enables the MAX17121. Drive EN high to start up the MAX17121 after a delay time, which is set by a capacitor at DLY.			
12	DLY	Startup Delay Setting. Connect a capacitor to adjust the delay based on $t_{DELAY} = C_{DLY} \times 410 k\Omega$.			
14, 21	GND	Ground			
15 DISH		VOFF Discharge Connection. Pulling DISH below ground activates an internal connection between VOFF and GND, rapidly discharging the VOFF supply. Typically, DISH is capacitively connected to VDD, so that when VDD falls, VOFF is discharged.			
16 VDD Supply Input. VDD 0.1μF capacitor.		Supply Input. VDD is the logic supply input for the scan driver. Bypass to GND through a minimum 0.1µF capacitor.			
18	VOFF Gate-Off Supply. VOFF is the negative supply voltage for the CKV_, CKVB_, and STVP high-vol driver outputs. Bypass to GND with a minimum of 1µF ceramic capacitor.				
19	Gate-On Supply VON is the positive supply voltage for the CKV CKVB and STVP high-voltage				

_Pin Description (continued)

PIN	NAME	FUNCTION
22	CKV1	High-Voltage Scan-Drive Output. When enabled, CKV1 toggles between its high state (connected to VON) and its low state (connected to VOFF) on each falling edge of the CPV1 input. Further, CKV1 is high impedance whenever CPV1 and STV are both low.
23	CKV1 Charge-Sharing Connection. CKVCS1 connects to CKVBCS1 whenever CPV1 and STV are both low (to make CKV1 and CKVB1 high impedance) to allow CKVB1 to connect to CKV1, sharing charge between the capacitive loads on these two outputs.	
24	CKVBCS1	CKVB1 Charge-Sharing Connection. CKVBCS1 connects to CKVCS1 whenever CPV1 and STV are both low (to make CKV1 and CKVB1 high impedance) to allow CKV1 to connect to CKVB1, sharing charge between the capacitive loads on these two outputs.
_	EP	Exposed Pad. EP is not connected in the IC. The EP should be connected to the ground plane on the PCB to improve thermal performance.

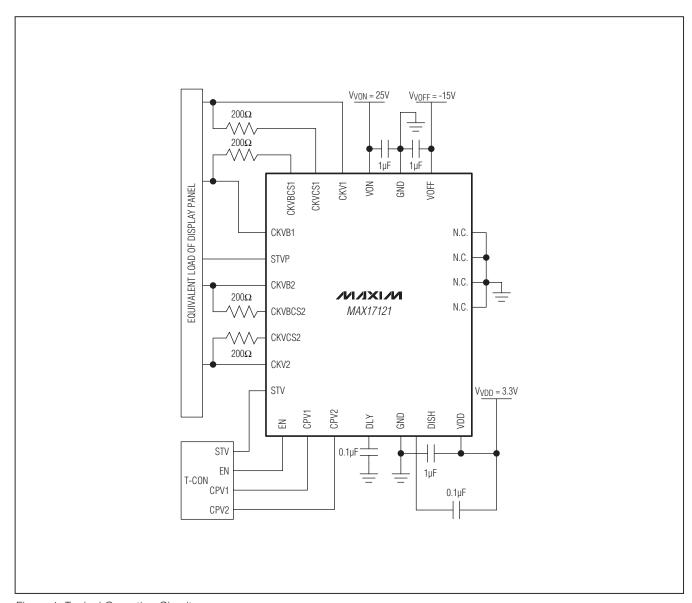


Figure 1. Typical Operating Circuit

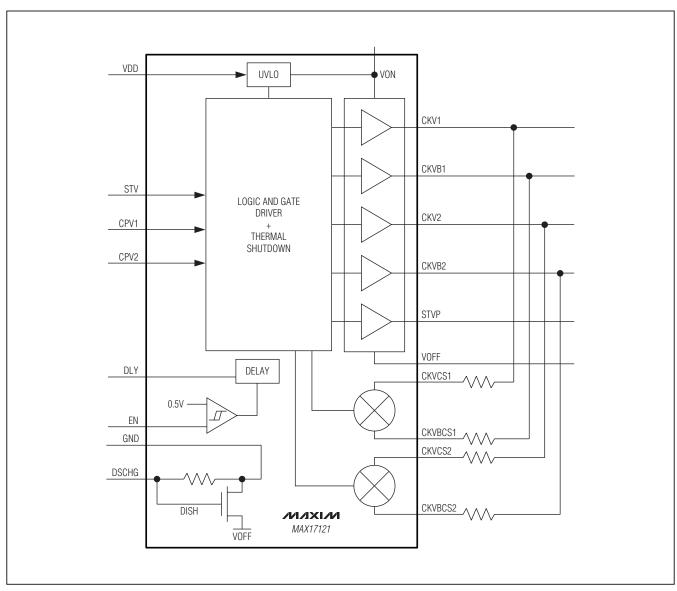


Figure 2. Functional Diagram

Detailed Description

The MAX17121 contains two high-voltage level-shifting scan drivers for active-matrix TFT LCDs. Figure 2 is the functional diagram.

Undervoltage Lockout on VDD

The undervoltage-lockout (VDD-UVLO) circuit on VDD compares the input voltage at VDD with the VDD-UVLO (2V typ) to ensure that the input voltage is high enough for reliable operation. There is 100mV of hysteresis to prevent supply transients from causing a restart. When

the VDD voltage is below VDD-UVLO, the scan-driver outputs are high impedance.

Undervoltage Lockout on VON

The undervoltage-lockout (VON-UVLO) circuit on VON compares the input voltage at VON with the VON-UVLO (12V typ) to ensure that the input voltage is high enough for reliable operation. There is 1V of hysteresis to prevent supply transients from causing a restart. When the VON voltage is below VON-UVLO, the scan-driver outputs are high impedance.

High-Voltage Level-Shifting Scan Driver

The MAX17121 includes 2 two-channel high-voltage level-shifting scan drivers. The scan-driver outputs (CKV1, CKV2, CKVB1, CKVB2, and STVP) swing between the power-supply rails (VON and VOFF) according to their corresponding input logic levels. The states of the CKV1, CKVB1, and STVP outputs are determined by the input logic levels present on STV and CPV1. The states of the CKV2 and CKVB2 outputs are determined by the input logic levels present on STV and CPV2 (see Figure 3, Table 1, and Table 2).

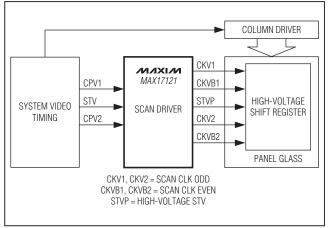


Figure 3. Scan-Driver System Diagram

STV comprises the vertical timing signals. CPV1 and CPV2 are the TFT gate-logic timing signals. These signals have CMOS input logic levels set by the VDD supply voltage. CKV1 and CKV2 are scan clock outputs, which are complementary to scan clock outputs CKVB1 and CKVB2, respectively. These output signals swing from VON to VOFF, which have a maximum upper level of +40V, a minimum lower level of -30V, and a combined maximum range of VON - VOFF = 65V. Their low-output impedance enables them to swiftly drive capacitive loads. Input pins CKVCS1, CKVBSC1, CKVSC2, and CKVBCS2 allow the charge in the panel equivalent capacitors to be shared. This reduces the power loss in state transition.

Table 1. STVP Logic

VON EN		V	INPUT S	OUTPUT	
VON	EN	VDLY	STV	CPV1	(STVP)
			L	X	L
	H	H*	Н	L	Н
> UVLO			Н	Н	High-Z
		L*	Χ	Х	L
		X	Χ	X	L
< UVLO	Χ	X	Χ	Χ	High-Z

H = high, L = low, High-Z = high impedance, X = don't care, $H^* = V_{DLY} > 1/2 \times V_{VDD}$, $L^* = V_{DLY} < 1/2 \times V_{VDD}$.

Table 2. CKV_, CKVB_ Logic

VON	ON EN V		INPUT SIGNALS		OUTPUTS						
VON EN	EIN	VDLY	STV	CPV_	CKV_	CKVB_	CHARGE SHARING				
	Н	H H*		L	L	High-Z	High-Z	Yes			
			Н	H `	□*	L	1	TOGGLE	TOGGLE	No	
> UVLO					н ''	н ''	''	''	''	Н	L
> UVLU			Н	Н	VON	VOFF	No				
		L*	X	X	VOFF	VOFF	No				
	Low	Х	X	X	VOFF	VOFF	No				
< UVLO	X	X	X	X	High-Z		No				

H = high, L = low, High-Z = high impedance, $\uparrow = rising edge$, X = don't care, $H^* = V_{DLY} > 1/2 \times V_{VDD}$, $L = V_{DLY} < 1/2 \times V_{VDD}$.

Enable Function

EN is an active-high logic input that enables/disables the MAX17121 output drive. Drive EN high to enable the MAX17121 scan driver. When EN is low, all the drivers' outputs are pulled to VOFF.

Delay Function

The DLY input sets the delay time in startup when the MAX17121 is enabled and the scan-driver outputs are enabled. The delay time is adjustable by choosing a different capacitor at DLY. Calculate the delay capacitance as:

$$CDLY = tDELAY/410k\Omega$$

The delay enable trip point is VVDD/2. Before VDLY reaches this threshold, scan-driver outputs stay in the same state as EN is low.

If there is no delay needed in the startup, connect DLY to VDD.

VOFF Rapid-Discharge Function (DISH Input)

The DISH input controls a switch between VOFF and GND. When DISH is pulled below ground by at least 1V, VOFF is rapidly discharged to GND. Typically, DISH is capacitively coupled to VDD so that if VDD falls suddenly, VOFF is quickly discharged to GND.

Thermal-Overload Protection

The thermal-overload protection prevents excessive power dissipation from overheating the device. When the junction temperature exceeds $T_J = +160^{\circ}\text{C}$, a thermal sensor immediately shuts down the scan-driver outputs. The outputs are set to high impedance. Once the device cools down by approximately 15°C, the device reactivates.

The thermal-overload protection protects the IC in the event of overheat conditions. For continuous operation, do not exceed the absolute maximum junction temperature rating of $T_{\text{J}} = +150^{\circ}\text{C}$.

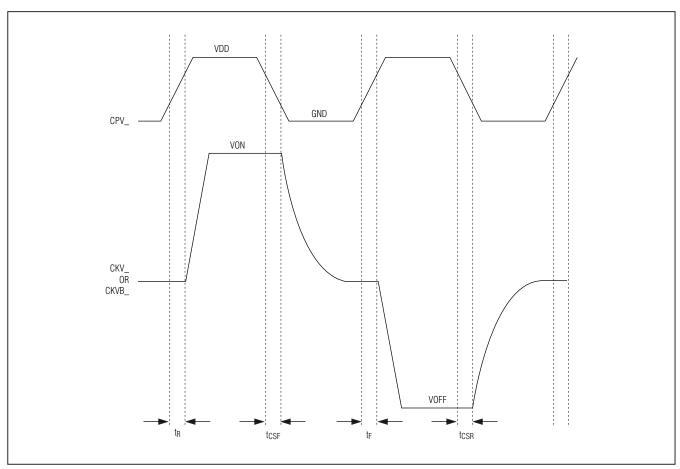


Figure 4. CKV Timing

_Applications Information

Power Dissipation

An IC's maximum power dissipation depends on the thermal resistance from the die to the ambient environment and the ambient temperature. The thermal resistance depends on the IC package, PCB copper area, other thermal mass, and airflow.

The MAX17121, with its exposed backside paddle soldered to 1in² of PCB copper, can dissipate approximately 27.8mW into +70°C still air. More PCB copper, cooler ambient air, and more airflow increase the possible dissipation, while less copper or warmer air decreases the IC's dissipation capability.

Scan-Driver Outputs

The power dissipated by the scan-driver outputs (CKV1, CKVB1, STVP, CKV2, and CKVB2) depends on the scan frequency, the capacitive load, and the difference between the VON and VOFF supply voltages. Assuming each output driver's the same capacitance, the power loss is:

$$PD_{SCAN} = 7 \times f_{SCAN} \times C_{PANEL} \times (V_{GON} - V_{GOFF})^2$$

where fSCAN is the scan frequency of the panel, CPANEL is the panel model capacitive load, VGON and VGOFF are the positive gate-on and negative gate-off voltages.

If all the scan drivers operate at a frequency of fSCAN = 50kHz, the load of the six outputs is CPANEL = 5nF, and the supply voltage difference is V_{VON} - V_{VOFF} = 30V, then the power dissipated is 1.125W.

PCB Layout and Grounding

Careful PCB layout is important for proper operation. Use the following guidelines for good PCB layout:

- Place the VON, VOFF, and VDD pin bypass capacitors as close as possible to the device. The ground connections of the VON, VOFF, and VDD bypass capacitors should be connected directly to the GND pin with a wide trace.
- Avoid using vias in the high-current paths. If vias are unavoidable, use many vias in parallel to reduce resistance and inductance.
- Connect the MAX17121's exposed paddle to the GND copper plane, and the copper plane area should be maximized to improve thermal dissipation.
- Minimize the length and maximize the width of the traces between the CKV, CKVB, and STV output nodes and the panel load for best transient responses.

Refer to the MAX17121 Evaluation Kit for an example of proper board layout.

_Chip Information

PROCESS: BiCMOS

_Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.		
24 TQFN-EP	T+2444	<u>21-0139</u>		

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